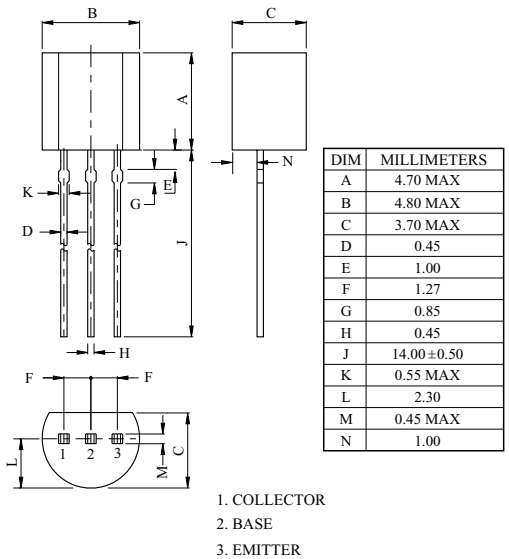
BC516

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE HIGH DARLINGTON TRANSISTOR.



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

1. COLLECTOR
2. BASE
3. EMITTER

TO-92

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-10	V
Collector Current	I_C	-500	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 ~ 150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-0.1mA, I_E=0	-40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-1.0mA, I_C=0	-10	-	-	V
Collector Cut-off Current	I_{CBO}	V_{CB}=-40V, I_E=0	-	-	-1.0	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-10V, I_C=0	-	-	-1.0	μA
DC Current Gain	h_{FE}	I_C=-100mA, V_{CE}=-2V	30k	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-1mA	-	-	-1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-100mA, I_B=-1mA	-	-1.5	-2.0	V
Current Gain Bandwidth Product	f_T	I_C=-100mA, V_{CE}=-2V, f=100MHz	-	220	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, f=1MHz, I_E=0	-	5.0	-	pF